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September 2015

# MOC3061M, MOC3062M, MOC3063M, MOC3162M, MOC3163M 6-Pin DIP Zero-Cross Triac Driver Optocoupler (600 Volt Peak)

#### **Features**

- Simplifies Logic Control of 115/240 VAC Power
- Zero Voltage Crossing to Minimize Conducted and Radiated Line Noise
- 600 V Peak Blocking Voltage
- Superior Static dv/dt
  - 600 V/µs (MOC306xM)
  - 1000 V/μs (MOC316xM)
- · Safety and Regulatory Approvals
  - UL1577, 4,170 VAC<sub>RMS</sub> for 1 Minute
  - DIN EN/IEC60747-5-5

## **Applications**

- Solenoid/Valve Controls
- · Static Power Switches
- · Temperature Controls
- · AC Motor Starters
- · Lighting Controls
- AC Motor Drives
- E.M. Contactors
- Solid State Relays

### Description

The MOC306XM and MOC316XM devices consist of a GaAs infrared emitting diode optically coupled to a monolithic silicon detector performing the function of a zero voltage crossing bilateral triac driver.

They are designed for use with a triac in the interface of logic systems to equipment powered from 115/240 VAC lines, such as solid-state relays, industrial controls, motors, solenoids and consumer appliances, etc.

Figure 2. Package Outlines

# 

(TRIAC SUBSTRATE)

Figure 1. Schematic

# **Safety and Insulation Ratings**

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE	< 150 V <sub>RMS</sub>	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–IV
Climatic Classification		40/85/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	V <sub>peak</sub>
V <sub>PR</sub>	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$ , 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1594	V <sub>peak</sub>
V <sub>IORM</sub>	Maximum Working Insulation Voltage	850	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	6000	V <sub>peak</sub>
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V	> 10 <sup>9</sup>	Ω

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A = 25^{\circ}$ C unless otherwise specified.

Symbol	Parameters	Device	Value	Unit
TOTAL DEV	/ICE			•
T <sub>STG</sub>	Storage Temperature	All	-40 to +150	°C
T <sub>OPR</sub>	Operating Temperature	All	-40 to +85	°C
TJ	Junction Temperature Range	All	-40 to +100	°C
T <sub>SOL</sub>	Lead Solder Temperature	All	260 for 10 seconds	°C
D	Total Device Power Dissipation at 25°C Ambient	All	250	mW
P <sub>D</sub>	Derate Above 25°C	All	2.94	mW/°C
EMITTER				
I <sub>F</sub>	Continuous Forward Current	All	60	mA
V <sub>R</sub>	Reverse Voltage	All	6	V
D	Total Power Dissipation at 25°C Ambient	All	120	mW
$P_{D}$	Derate Above 25°C	All	1.41	mW/°C
DETECTOR	R			
$V_{DRM}$	Off-State Output Terminal Voltage	All	600	V
I <sub>TSM</sub>	Peak Non-Repetitive Surge Current (Single Cycle 60 Hz Sine Wave)	All	1	А
D	Total Power Dissipation at 25°C Ambient	All	150	mW
P <sub>D</sub>	Derate Above 25°C	All	1.76	mW/°C

### **Electrical Characteristics**

 $T_A = 25$ °C unless otherwise specified.

#### **Individual Component Characteristics**

Symbol	Parameters	Test Conditions	Device	Min.	Тур.	Max.	Unit
EMITTER							
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 30 mA	All		1.3	1.5	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 6 V	All		0.005	100	μΑ
DETECTO	OR .						
	Peak Blocking Current,	$V_{DDM} = 600 \text{ V. } I_{E} = 0^{(1)}$	MOC306XM		10	500	nA
DRM1	IDRM1 Either Direction		MOC316XM		10	100	ΠA
dv/dt	Critical Rate of Rise of	Critical Rate of Rise of	MOC306XM	600	1500		\//u.o
uv/ut	Off-State Voltage	$I_F = 0 \text{ (Figure 11)}^{(2)}$	MOC316XM	1000			V/μs

#### **Transfer Characteristics**

Symbol	DC Characteristics	Test Conditions	Device	Min.	Тур.	Max.	Unit
			MOC3061M			15	
I <sub>FT</sub>	LED Trigger Current (Rated I <sub>FT</sub> )	Main Terminal Voltage = 3 V <sup>(3)</sup>	MOC3062M MOC3162M			10	mA
	(Nateu IFT)	vollage = e v	MOC3063M MOC3163M			5	
V <sub>TM</sub>	Peak On-State Voltage, Either Direction	I <sub>TM</sub> = 100 mA peak, I <sub>F</sub> = rated I <sub>FT</sub>	All		1.8	3.0	V
I <sub>H</sub>	Holding Current, Either Direction		All		500		μΑ

#### **Zero Crossing Characteristics**

Symbol	Characteristics	Test Conditions	Device	Min.	Тур.	Max.	Unit
			MOC3061M				
	Inhibit Voltage (MT1-MT2		MOC3062M		12	20	
$V_{INH}$	voltage above which	I <sub>F</sub> = rated I <sub>FT</sub>	MOC3063M				V
	device will not trigger)		MOC3162M		10	15	
			MOC3163M		12	15	/
I <sub>DRM2</sub>	Leakage in Inhibited State	$I_F$ = rated $I_{FT}$ , $DRM$ = 600 V, off-state	All			2	mA

#### **Isolation Characteristics**

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V <sub>ISO</sub>	Isolation Voltage <sup>(4)</sup>	f = 60 Hz, t = 1 Minute	4170			$VAC_{RMS}$
R <sub>ISO</sub>	Isolation Resistance	V <sub>I-O</sub> = 500 V <sub>DC</sub>		10 <sup>11</sup>		Ω
C <sub>ISO</sub>	Isolation Capacitance	V = 0 V, f = 1 MHz		0.2		pF

#### Notes:

- 1. Test voltage must be applied within dv/dt rating.
- 2. This is static dv/dt. See Figure 11 for test circuit. Commutating dv/dt is a function of the load-driving thyristor(s) only.
- 3. All devices are guaranteed to trigger at an  $I_F$  value less than or equal to max  $I_{FT}$ . Therefore, recommended operating  $I_F$  lies between max  $I_{FT}$  (15 mA for MOC3061M, 10 mA for MOC3062M and MOC3162M, 5 mA for MOC3063M and MOC3163M) and absolute maximum  $I_F$  (60 mA).
- 4. Isolation voltage,  $V_{ISO}$ , is an internal device dielectric breakdown rating. For this test, pins 1 and 2 are common, and pins 4, 5 and 6 are common.

# **Typical Performance Curves**

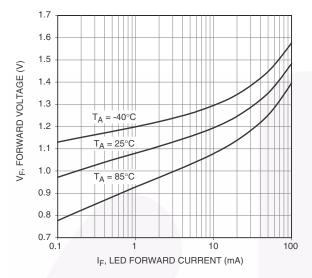


Figure 3. LED Forward Voltage vs. Forward Current

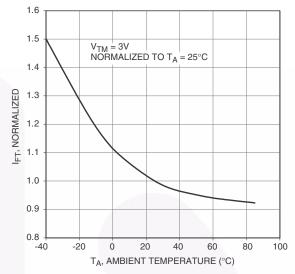


Figure 4. Trigger Current Vs. Temperature

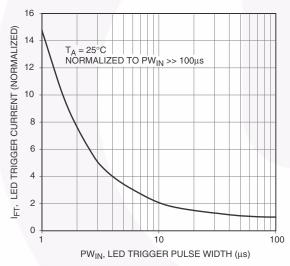


Figure 5. LED Current Required to Trigger vs. LED Pulse Width

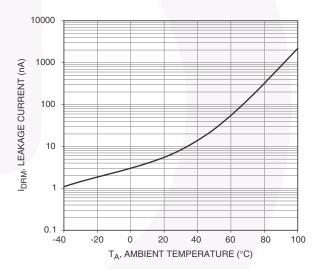


Figure 6. Leakage Current, IDRM vs. Temperature

# Typical Performance Curves (Continued)

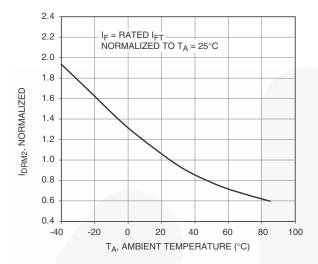


Figure 7. I<sub>DRM2</sub>, Leakage in Inhibit State vs. Temperature

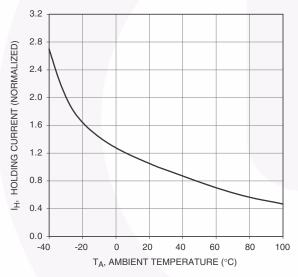


Figure 9. I<sub>H</sub>, Holding Current vs. Temperature

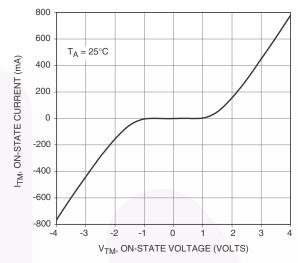


Figure 8. On-State Characteristics

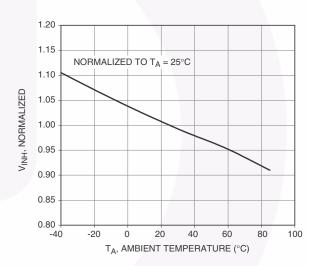


Figure 10. Inhibit Voltage vs. Temperature

- 1. 100x scope probes are used, to allow high speeds and voltages.
- 2. The worst-case condition for static dv/dt is established by triggering the D.U.T. with a normal LED input current, then removing the current. The variable vernier resistor combined with various capacitor combinations allows the dv/dt to be gradually increased until the D.U.T. continues to trigger in response to the applied voltage pulse, even after the LED current has been removed. The dv/dt is then decreased until the D.U.T. stops triggering. t<sub>RC</sub> is measured at this point and recorded.

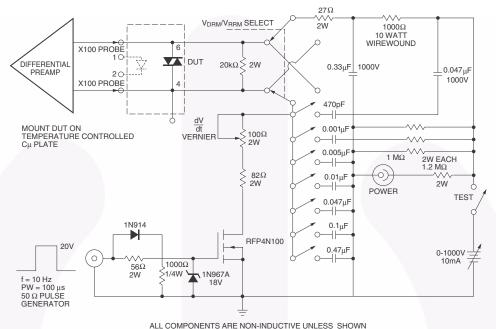


Figure 11. Circuit for Static  $\frac{dV}{dt}$  Measurement of Power Thyristors

## **Basic Applications**

Typical circuit for use when hot line switching is required. In this circuit the "hot" side of the line is switched and the load connected to the cold or neutral side. The load may be connected to either the neutral or hot line.

 $R_{in}$  is calculated so that  $I_{\textrm{F}}$  is equal to the rated  $I_{\textrm{FT}}$  of the part, 15mA for the MOC3061M, 10mA for the MOC3062M, or 5mA for the MOC3063M. The  $39\Omega$  resistor and  $0.01\mu\textrm{F}$  capacitor are for snubbing of the triac and is often, but not always, necessary depending upon the particular triac and load used.

Suggested method of firing two, back-to-back SCR's with a Fairchild triac driver. Diodes can be 1N4001; resistors, R1 and R2, are optional  $330\Omega$ .

#### Note:

This optoisolator should not be used to drive a load directly. It is intended to be a trigger device only.

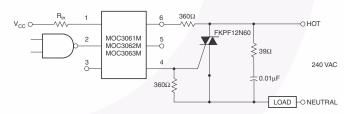


Figure 12. Hot-Line Switching Application Circuit

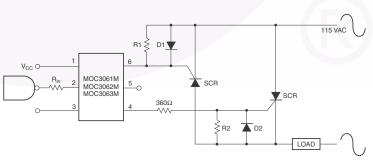
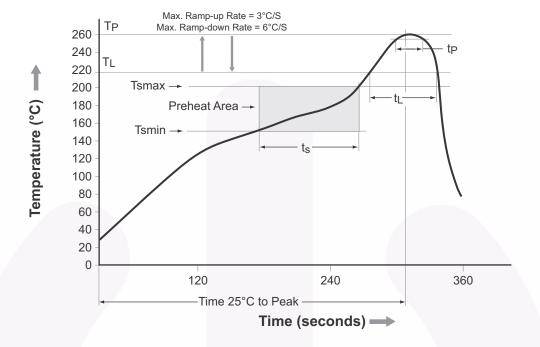


Figure 13. Inverse-Parallel SCR Driver Circuit

# **Reflow Profile**



Profile Freature	Pb-Free Assembly Profile	
Temperature Minimum (Tsmin)	150°C	
Temperature Maximum (Tsmax)	200°C	
Time (t <sub>S</sub> ) from (Tsmin to Tsmax)	60 seconds to 120 seconds	
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/second maximum	
Liquidous Temperature (T <sub>L</sub> )	217°C	
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 seconds to 150 seconds	
Peak Body Package Temperature	260°C +0°C / –5°C	
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds	
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second maximum	
Time 25°C to Peak Temperature	8 minutes maximum	

Figure 14. Reflow Profile

# Ordering Information(5)

Part Number	Package	Packing Method
MOC3061M	DIP 6-Pin	Tube (50 Units)
MOC3061SM	SMT 6-Pin (Lead Bend)	Tube (50 Units)
MOC3061SR2M	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
MOC3061VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
MOC3061SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
MOC3061SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
MOC3061TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

#### Note:

5. The product orderable part number system listed in this table also applies to the MOC3062M, MOC3063M, MOC3162M, and MOC3163M product families.

# **Marking Information**

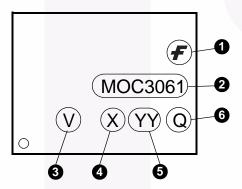
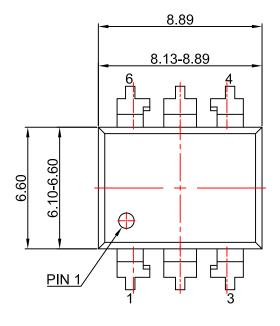
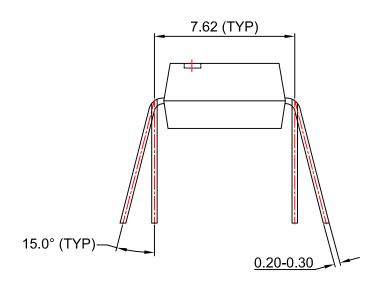
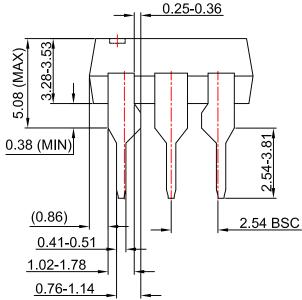


Figure 15. Top Mark

Top Mark Definitions					
1	Fairchild Logo				
2	Device Number				
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)				
4	One-Digit Year Code, e.g., '5'				
5	Two-Digit Work Week, Ranging from '01' to '53'				
6	Assembly Package Code				



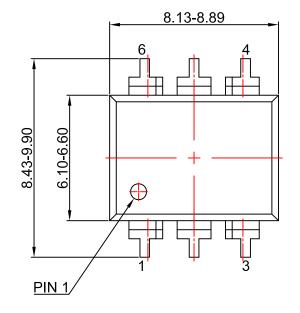


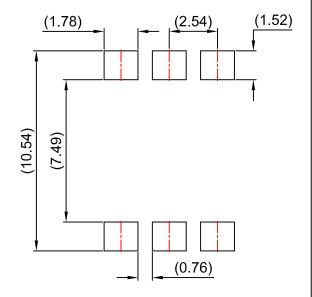


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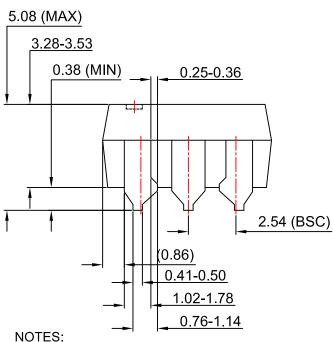
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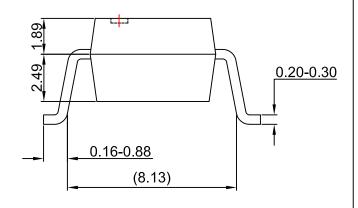






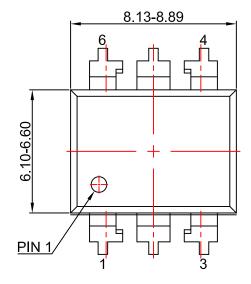
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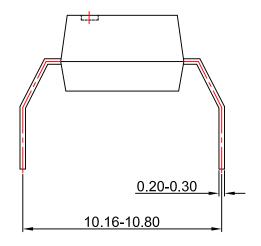


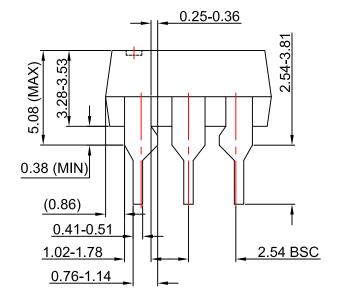


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